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May 2014

FDMS7602S

Dual N-Channel PowerTrench[®] MOSFET

Q1: 30 V, 30 A, 7.5 mΩ Q2: 30 V, 30 A, 5.0 mΩ

Features

Q1: N-Channel

■ Max $r_{DS(on)}$ = 7.5 mΩ at V_{GS} = 10 V, I_D = 12 A

■ Max $r_{DS(on)}$ = 12 mΩ at V_{GS} = 4.5 V, I_D = 10 A

Q2: N-Channel

■ Max $r_{DS(on)}$ = 5.0 mΩ at V_{GS} = 10 V, I_D = 17 A

■ Max $r_{DS(on)}$ = 6.8 mΩ at V_{GS} = 4.5 V, I_D = 14 A

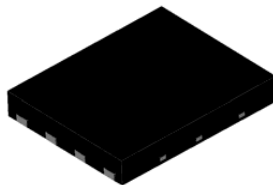
■ RoHS Compliant

General Description

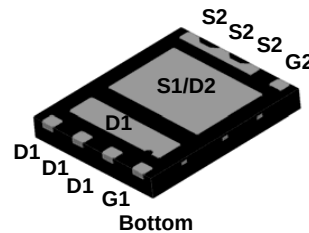
This device includes two specialized N-Channel MOSFETs in a dual MLP package. The switch node has been internally connected to enable easy placement and routing of synchronous buck converters. The control MOSFET (Q1) and synchronous SyncFET[™] (Q2) have been designed to provide optimal power efficiency.

Applications

- Computing
- Communications
- General Purpose Point of Load
- Notebook VCore

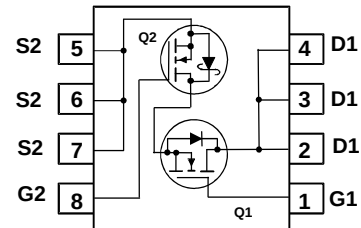


Top



Bottom

Power 56



MOSFET Maximum Ratings $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Q1	Q2	Units
V_{DS}	Drain to Source Voltage	30	30	V
V_{GS}	Gate to Source Voltage (Note 3)	± 20	± 20	V
I_D	Drain Current -Continuous $T_C = 25^\circ\text{C}$	30	30	A
	-Continuous $T_A = 25^\circ\text{C}$	12 ^{1a}	17 ^{1b}	
	-Pulsed	40	60	
P_D	Power Dissipation for Single Operation $T_A = 25^\circ\text{C}$	2.2 ^{1a}	2.5 ^{1b}	W
	Power Dissipation for Single Operation $T_A = 25^\circ\text{C}$	1.0 ^{1c}	1.0 ^{1d}	
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +150		$^\circ\text{C}$

Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	57 ^{1a}	50 ^{1b}	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	125 ^{1c}	120 ^{1d}	
$R_{\theta JC}$	Thermal Resistance, Junction to Case	3.5	2	

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDMS7602S	FDMS7602S	Power 56	13 "	12 mm	3000 units

Electrical Characteristics $T_J = 25\text{ }^{\circ}\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Type	Min	Typ	Max	Units
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Off Characteristics

BV_{DSS}	Drain to Source Breakdown Voltage	$I_D = 250\text{ }\mu\text{A}$, $V_{GS} = 0\text{ V}$ $I_D = 1\text{ mA}$, $V_{GS} = 0\text{ V}$	Q1 Q2	30 30			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\text{ }\mu\text{A}$, referenced to $25\text{ }^{\circ}\text{C}$ $I_D = 1\text{ mA}$, referenced to $25\text{ }^{\circ}\text{C}$	Q1 Q2		15 15		mV/ $^{\circ}\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 24\text{ V}$, $V_{GS} = 0\text{ V}$	Q1 Q2			1 500	μA μA
I_{GSS}	Gate to Source Leakage Current	$V_{GS} = 20\text{ V}$, $V_{DS} = 0\text{ V}$ $V_{GS} = 20\text{ V}$, $V_{DS} = 0\text{ V}$	Q1 Q2			100 100	nA nA

On Characteristics

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}$, $I_D = 250\text{ }\mu\text{A}$ $V_{GS} = V_{DS}$, $I_D = 1\text{ mA}$	Q1 Q2	1 1	1.8 1.8	3 3	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D = 250\text{ }\mu\text{A}$, referenced to $25\text{ }^{\circ}\text{C}$ $I_D = 1\text{ mA}$, referenced to $25\text{ }^{\circ}\text{C}$	Q1 Q2		-6 -5		mV/ $^{\circ}\text{C}$
$r_{DS(on)}$	Drain to Source On Resistance	$V_{GS} = 10\text{ V}$, $I_D = 12\text{ A}$	Q1		6.0	7.5	m Ω
		$V_{GS} = 4.5\text{ V}$, $I_D = 10\text{ A}$			8.5	12	
		$V_{GS} = 10\text{ V}$, $I_D = 12\text{ A}$, $T_J = 125\text{ }^{\circ}\text{C}$	Q2		8.3	12	
		$V_{GS} = 10\text{ V}$, $I_D = 17\text{ A}$ $V_{GS} = 4.5\text{ V}$, $I_D = 14\text{ A}$ $V_{GS} = 10\text{ V}$, $I_D = 17\text{ A}$, $T_J = 125\text{ }^{\circ}\text{C}$			4.2 5.4 4.9	5.0 6.8 7.2	
g_{FS}	Forward Transconductance	$V_{DS} = 5\text{ V}$, $I_D = 12\text{ A}$	Q1		63		S
		$V_{DS} = 5\text{ V}$, $I_D = 17\text{ A}$	Q2		87		

Dynamic Characteristics

C_{iss}	Input Capacitance	Q1: $V_{DS} = 15\text{ V}$, $V_{GS} = 0\text{ V}$, $f = 1\text{ MHz}$	Q1 Q2		1315 2020	1750 2690	pF
C_{oss}	Output Capacitance	Q2: $V_{DS} = 15\text{ V}$, $V_{GS} = 0\text{ V}$, $f = 1\text{ MHz}$	Q1 Q2		445 860	600 1145	pF
C_{rss}	Reverse Transfer Capacitance		Q1 Q2		45 95	70 145	pF
R_g	Gate Resistance		Q1 Q2		0.9 0.7		Ω

Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	Q1: $V_{DD} = 15\text{ V}$, $I_D = 12\text{ A}$, $R_{GEN} = 6\text{ }\Omega$ Q2: $V_{DD} = 15\text{ V}$, $I_D = 17\text{ A}$, $R_{GEN} = 6\text{ }\Omega$	Q1 Q2		8.6 11	18 20	ns
t_r	Rise Time		Q1 Q2		2.5 3.8	10 10	ns
$t_{d(off)}$	Turn-Off Delay Time		Q1 Q2		20 27	32 43	ns
t_f	Fall Time		Q1 Q2		2.3 3.2	10 10	ns
Q_g	Total Gate Charge	$V_{GS} = 0\text{ V}$ to 10 V	Q1 Q2		20 33	28 46	nC
Q_g	Total Gate Charge	$V_{GS} = 0\text{ V}$ to 4.5 V	Q1 Q2		9.3 16	13 22	nC
Q_{gs}	Gate to Source Gate Charge	Q2 $V_{DD} = 15\text{ V}$, $I_D = 17\text{ A}$	Q1 Q2		4.3 5.8		nC
Q_{gd}	Gate to Drain "Miller" Charge		Q1 Q2		2.2 4.6		nC

Electrical Characteristics $T_J = 25\text{ }^{\circ}\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Type	Min	Typ	Max	Units
Drain-Source Diode Characteristics							
V_{SD}	Source to Drain Diode Forward Voltage	$V_{GS} = 0\text{ V}$, $I_S = 12\text{ A}$ (Note 2) $V_{GS} = 0\text{ V}$, $I_S = 17\text{ A}$ (Note 2)	Q1 Q2		0.8 0.8	1.2 1.2	V
t_{rr}	Reverse Recovery Time	Q1 $I_F = 12\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$	Q1 Q2		27 29	43 46	ns
Q_{rr}	Reverse Recovery Charge	Q2 $I_F = 17\text{ A}$, $di/dt = 300\text{ A}/\mu\text{s}$	Q1 Q2		10 31	18 50	nC

Notes:

1: $R_{\theta JA}$ is determined with the device mounted on a 1 in² pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



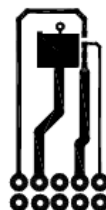
a. 57 $^{\circ}\text{C}/\text{W}$ when mounted on a 1 in² pad of 2 oz copper



b. 50 $^{\circ}\text{C}/\text{W}$ when mounted on a 1 in² pad of 2 oz copper



c. 125 $^{\circ}\text{C}/\text{W}$ when mounted on a minimum pad of 2 oz copper



d. 120 $^{\circ}\text{C}/\text{W}$ when mounted on a minimum pad of 2 oz copper

2: Pulse Test: Pulse Width < 300 μs , Duty cycle < 2.0%.

3: As an N-ch device, the negative V_{GS} rating is for low duty cycle pulse occurrence only. No continuous rating is implied.

Typical Characteristics (Q1 N-Channel) $T_J = 25^\circ\text{C}$ unless otherwise noted

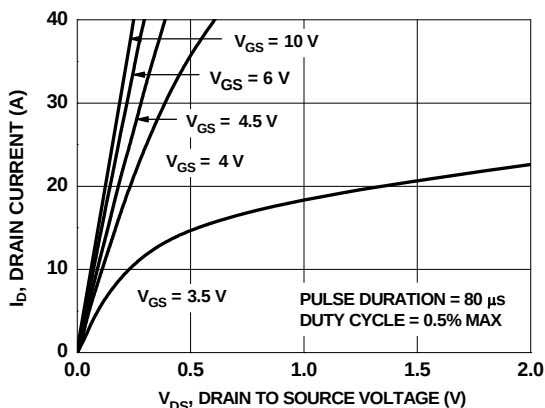


Figure 1. On Region Characteristics

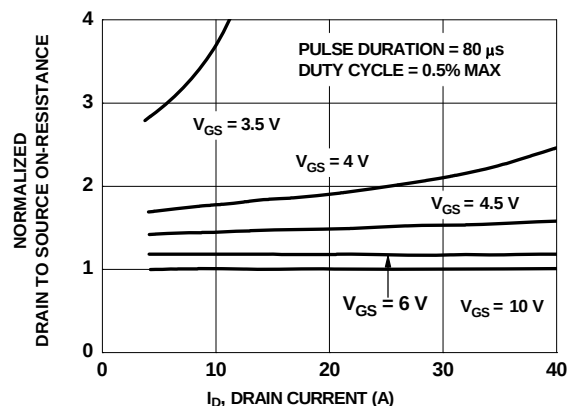


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

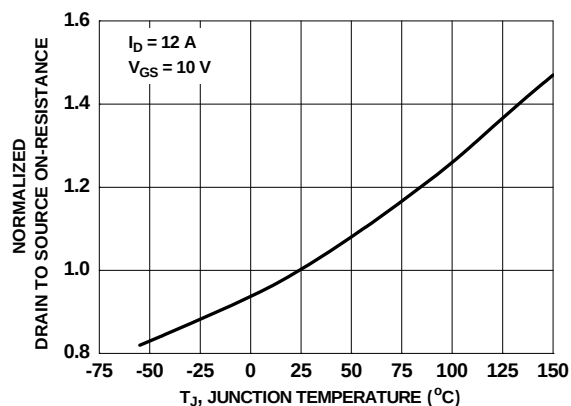


Figure 3. Normalized On Resistance vs Junction Temperature

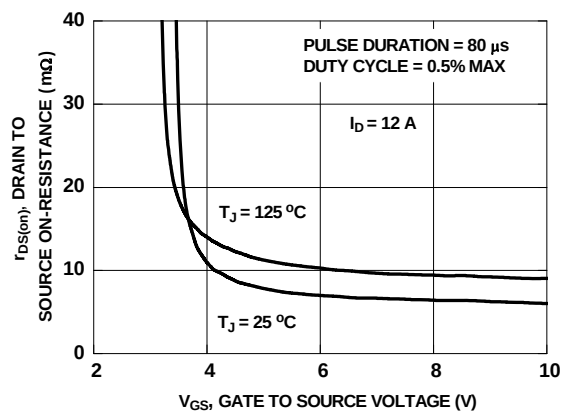


Figure 4. On-Resistance vs Gate to Source Voltage

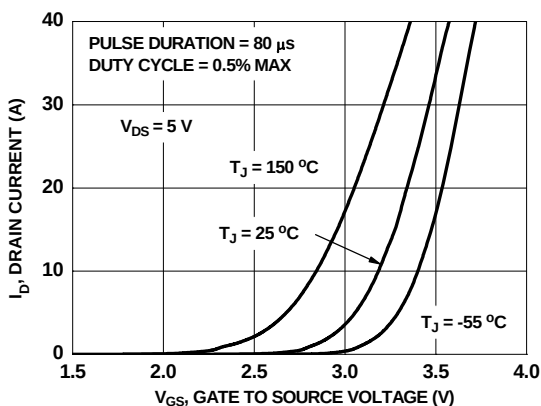


Figure 5. Transfer Characteristics

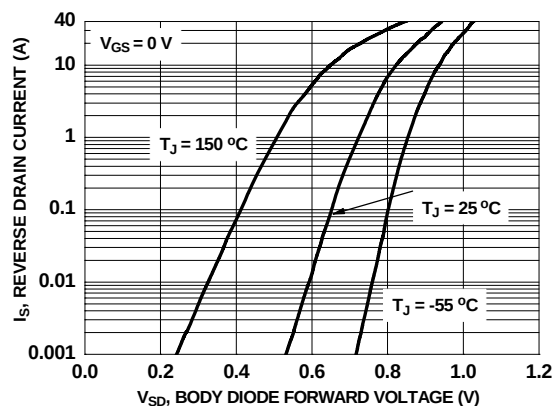


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

Typical Characteristics (Q1 N-Channel) $T_J = 25^\circ\text{C}$ unless otherwise noted

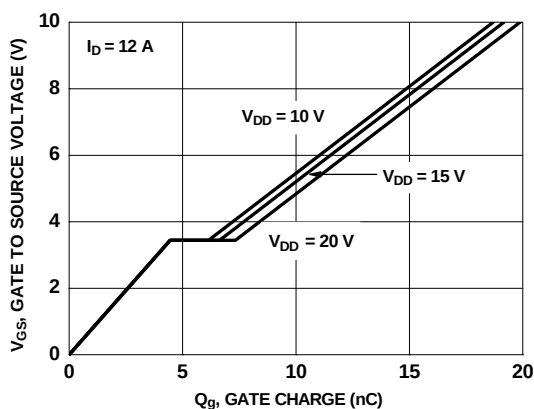


Figure 7. Gate Charge Characteristics

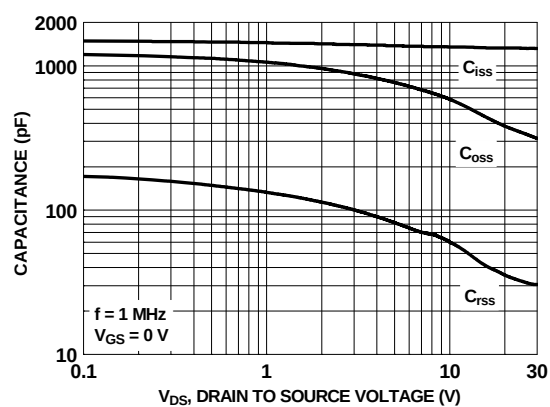


Figure 8. Capacitance vs Drain to Source Voltage

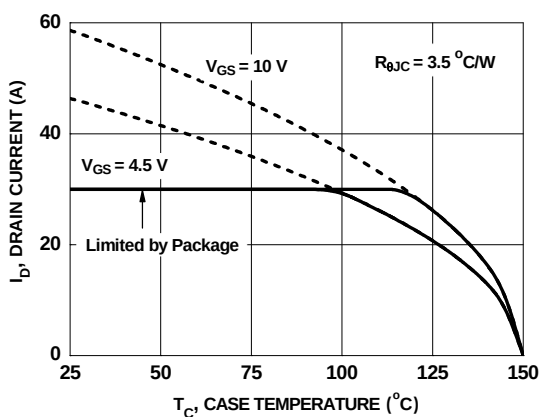


Figure 9. Maximum Continuous Drain Current vs Case Temperature

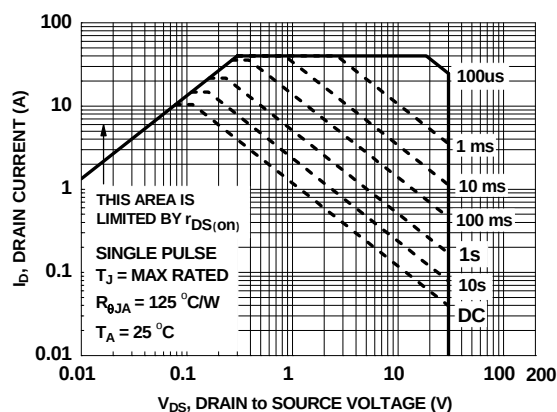


Figure 10. Forward Bias Safe Operating Area

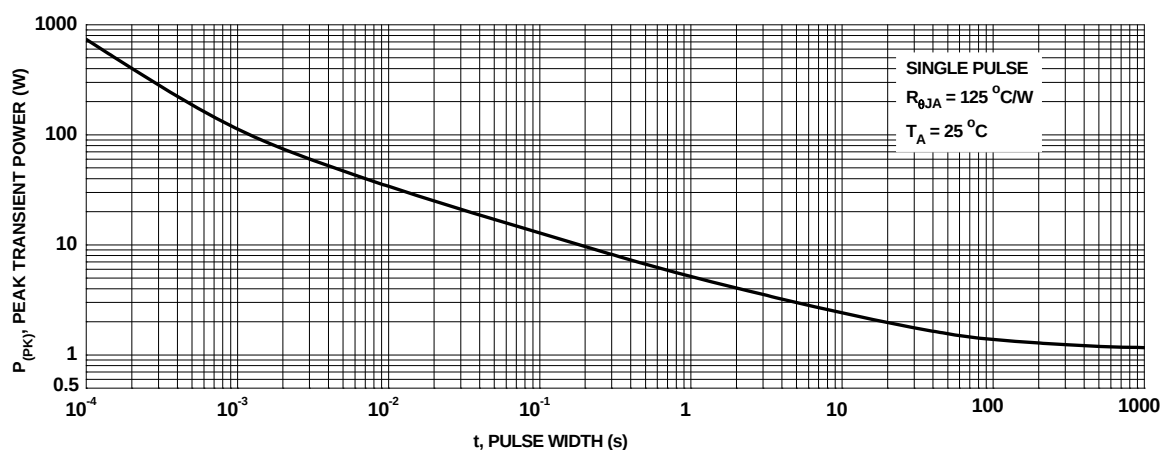


Figure 11. Single Pulse Maximum Power Dissipation

Typical Characteristics (Q1 N-Channel) $T_J = 25^\circ\text{C}$ unless otherwise noted

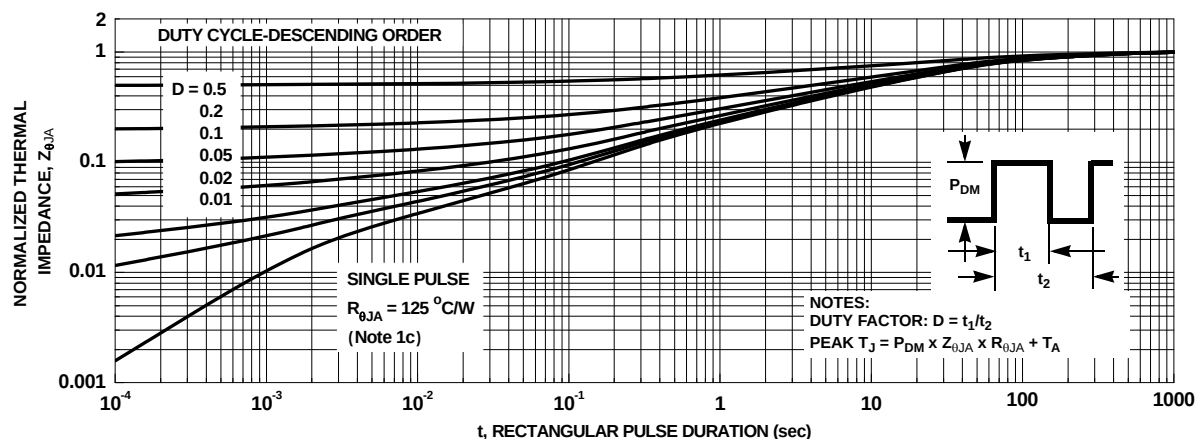


Figure 12. Junction-to-Ambient Transient Thermal Response Curve

Typical Characteristics (Q2 SyncFET)

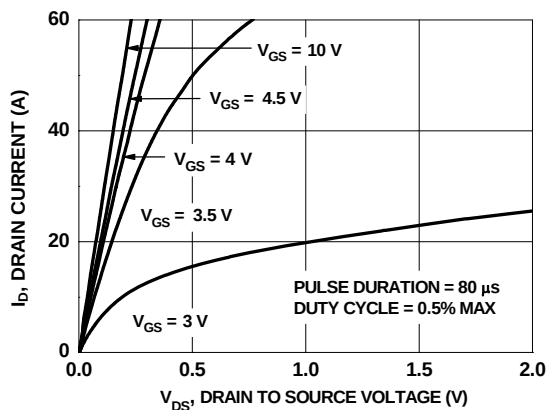


Figure 13. On-Region Characteristics

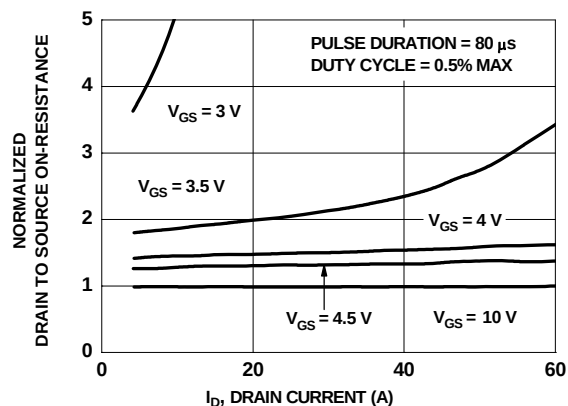


Figure 14. Normalized on-Resistance vs Drain Current and Gate Voltage

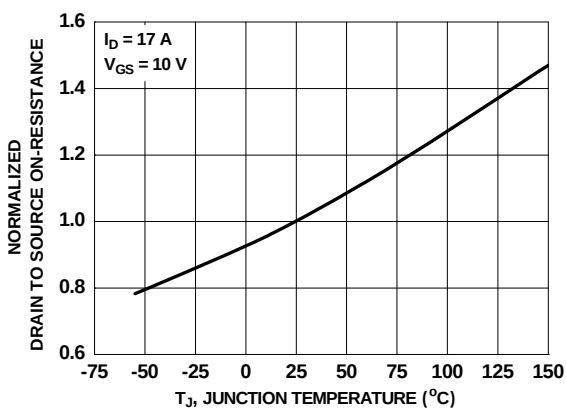


Figure 15. Normalized On-Resistance vs Junction Temperature

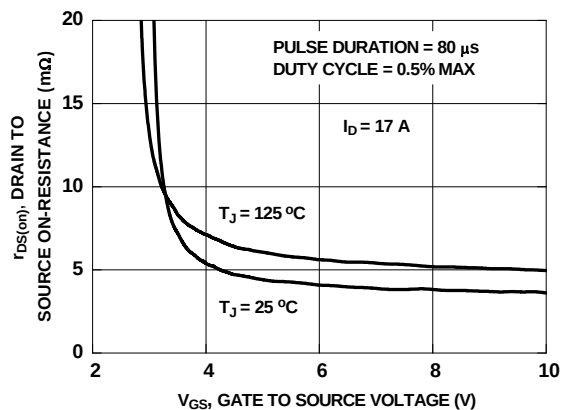


Figure 16. On-Resistance vs Gate to Source Voltage

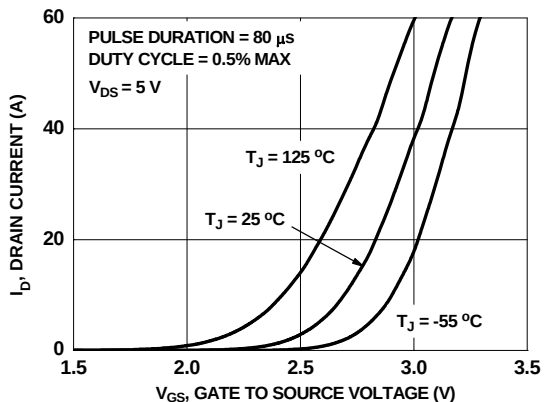


Figure 17. Transfer Characteristics

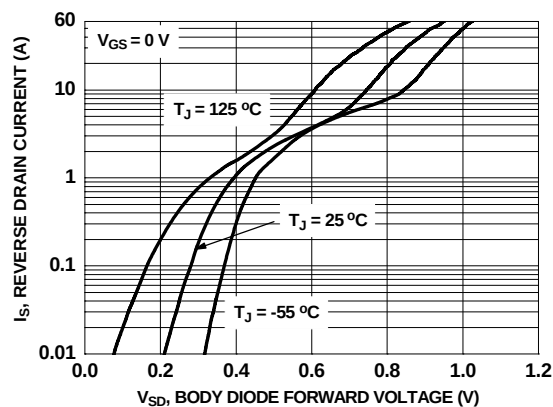


Figure 18. Source to Drain Diode Forward Voltage vs Source Current

Typical Characteristics (Q2 SyncFET)

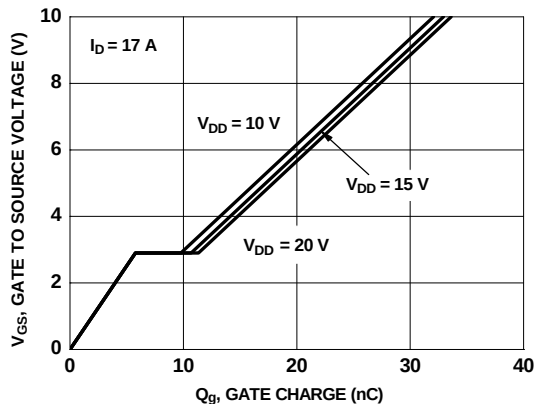


Figure 19. Gate Charge Characteristics

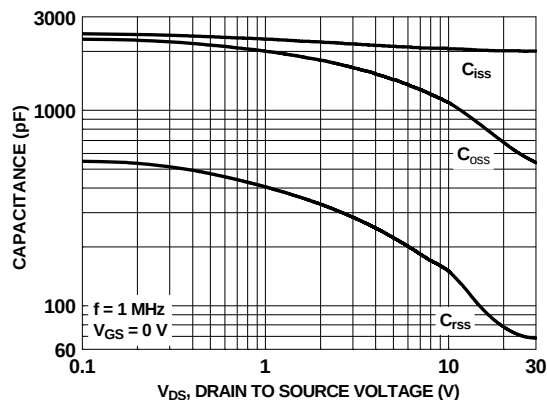


Figure 20. Capacitance vs Drain to Source Voltage

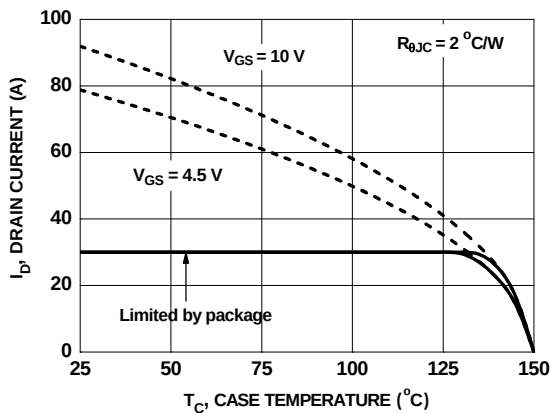


Figure 21. Maximum Continuous Drain Current vs Case Temperature

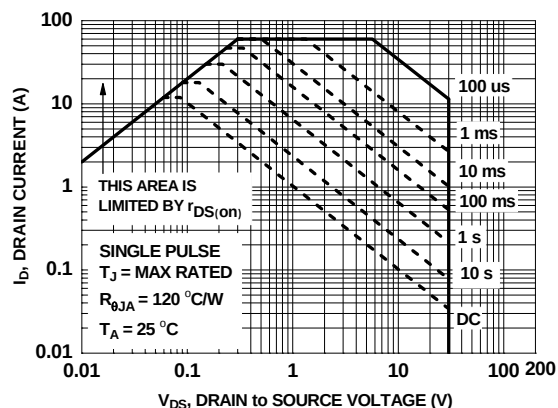


Figure 22. Forward Bias Safe Operating Area

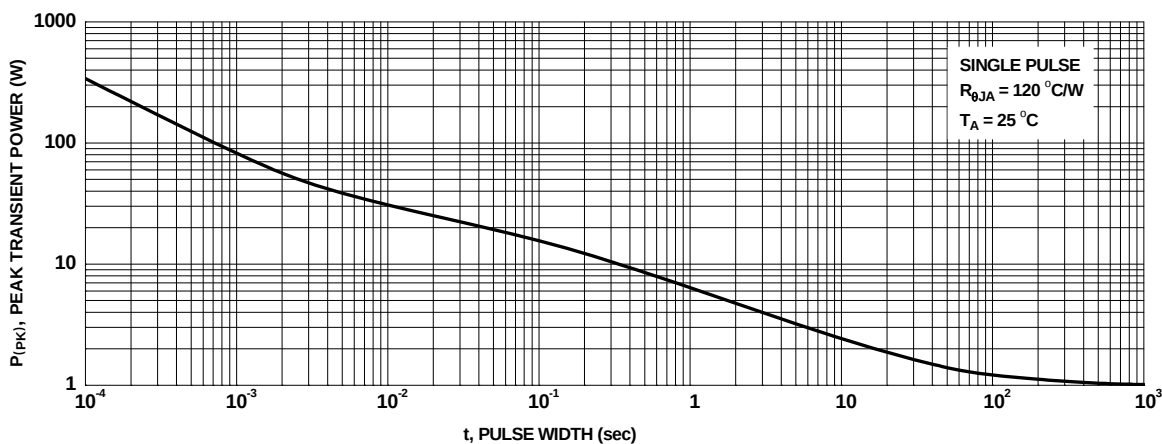


Figure 23. Single Pulse Maximum Power Dissipation

Typical Characteristics (Q2 SyncFET)

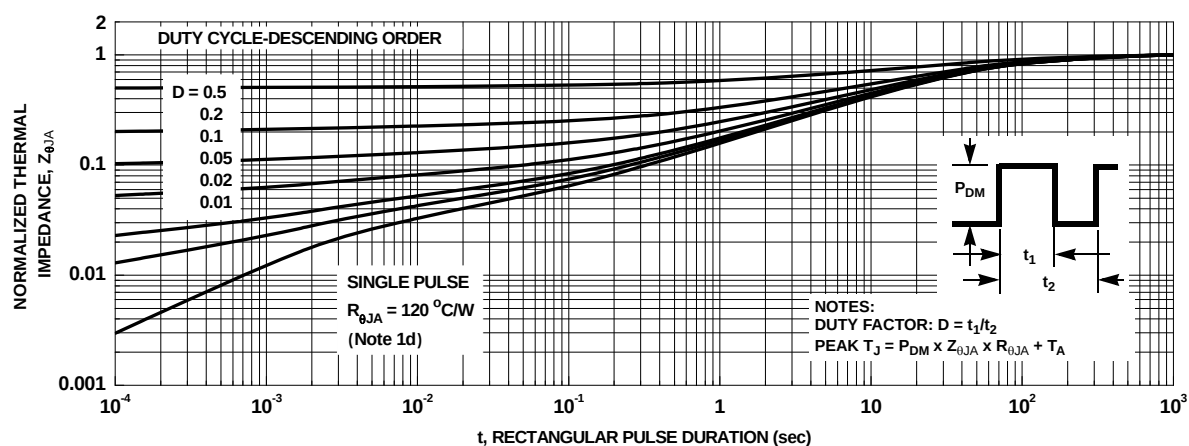


Figure 24. Junction-to-Ambient Transient Thermal Response Curve

Typical Characteristics (continued)

SyncFET[™] Schottky body diode Characteristics

Fairchild's SyncFET[™] process embeds a Schottky diode in parallel with PowerTrench[®] MOSFET. This diode exhibits similar characteristics to a discrete external Schottky diode in parallel with a MOSFET. Figure 25 shows the reverse recovery characteristic of the FDMS7602S.

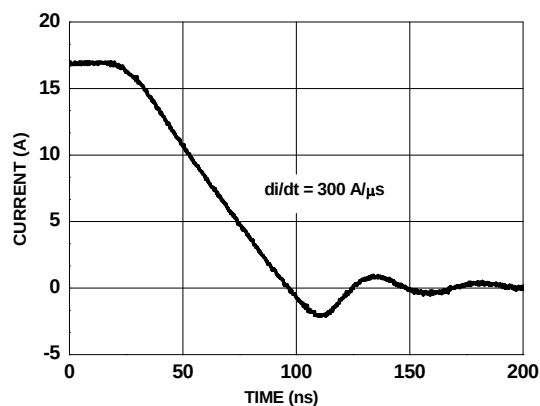


Figure 25. FDMS7602S SyncFET[™] Body Diode Reverse Recovery Characteristic

Schottky barrier diodes exhibit significant leakage at high temperature and high reverse voltage. This will increase the power in the device.

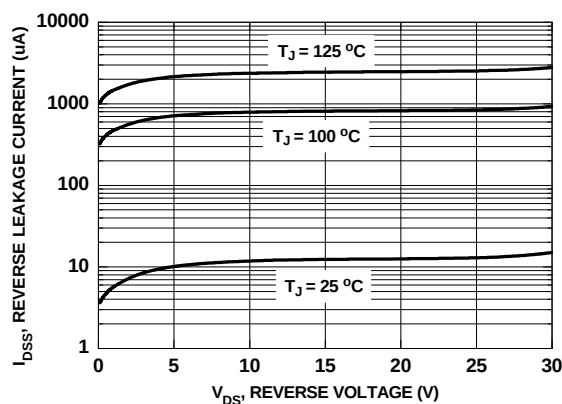
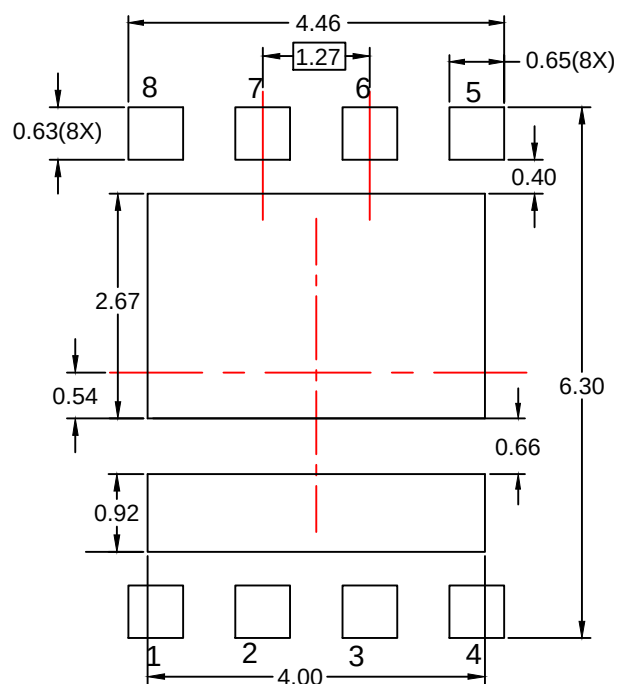
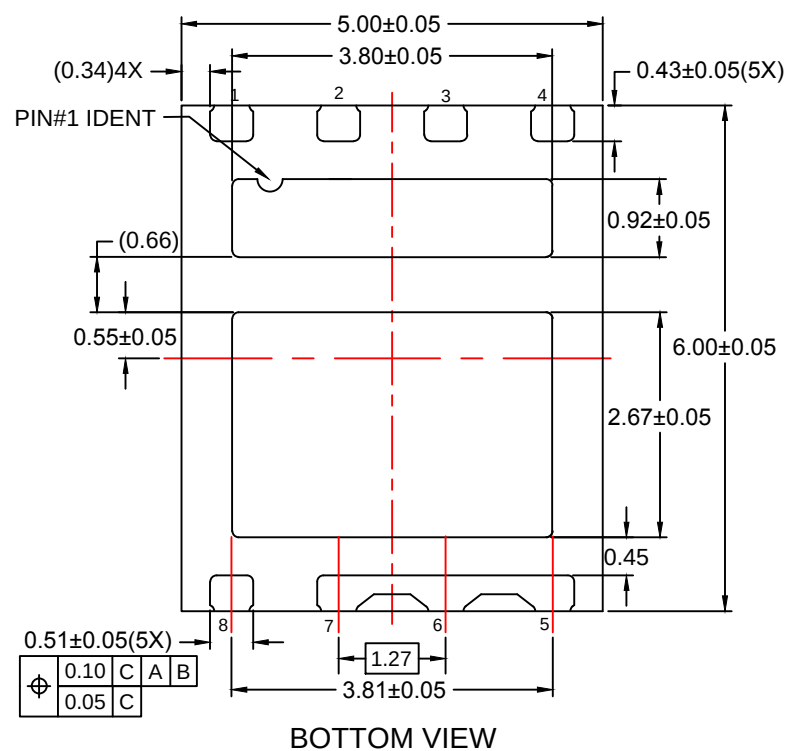


Figure 26. SyncFET[™] Body Diode Reverse Leakage vs. Drain-Source Voltage



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